

ABSTRACT

PRECURSOR SOLUTION FOR THIN FILM DEPOSITION AND THIN FILM FORMING METHOD USING SAME

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The present invention relates to a precursor solution for thin-film deposition including a functional solvent selected from among liquid alkene and liquid alkyne capable of dissolving a metal halide at room temperature and a metal
10 halide dissolved in the functional solvent and existing as a liquid at room temperature, thereby solving problems caused by halogen gas generated in a chamber during a deposition process and improving the uniformity of the thickness of a thin film.

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(FIG. 2)